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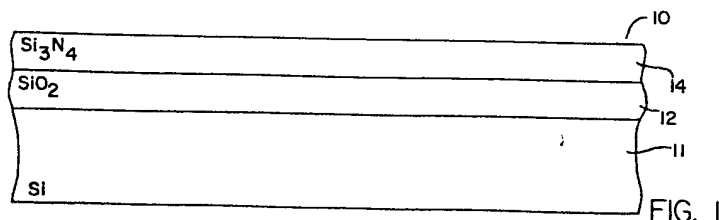
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54 **Process of manufacturing a bipolar transistor.**

57 A process for forming a buried layer 22 comprises the steps of covering a wafer (10) with a silicon dioxide layer (18). Dopants are introduced into the silicon dioxide layer (18) via an ion implantation process. Thereafter, a second silicon dioxide layer (20) is grown on the first silicon dioxide layer (18) and the wafer (10) is then subjected to a heating process which serves to both anneal the silicon wafer and drive dopants implanted into the first silicon dioxide layer (18) into

the silicon wafer. In this way, crystal lattice damage which normally accompanies ion implantation is avoided. The second silicon dioxide layer (20) prevents out diffusion of the implanted ions from the first silicon dioxide layer (18) into the atmosphere. The first and second silicon dioxide layers (18,20) are then removed and an epitaxial layer (24) is formed on the wafer (10). A base region (48) and emitter region (46) are then formed in the epitaxial layer (24).



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PROCESS OF MANUFACTURING A BIPOLAR TRANSISTOR  
DESCRIPTION

This invention relates to the manufacture of a bipolar transistor having a buried layer.

It is known in the art to dope regions in a silicon wafer using ion implantation. While ion implantation is an effective method for providing doped regions, ion implantation processes cause crystal lattice defects in silicon. Such defects can hinder operation of semiconductor devices by causing leakage currents. In addition, crystal lattice defects can degrade layers of silicon dioxide subsequently grown on wafers. Obviously, the higher the dopant concentration used during ion implantation, the greater the defect density produced thereby. Accordingly, there is a trade off that must take place between the amount of resistivity desired and the crystal defect concentration that can be tolerated.

Defects produced by ion implantation can be removed by an annealing process during which silicon is typically heated to a temperature of about 1,000°C for an amount of time dependent on the process involved. Unfortunately, during such processes, dopants can escape from the silicon wafer into the atmosphere. This is known as out diffusion.

It is also known in the art to dope regions in a silicon wafer by forming a mask layer on the wafer, and forming a window region in the mask layer, thereby exposing a portion of the underlying silicon. The mask layer typically includes a silicon dioxide layer covered with a silicon nitride layer. A  $Sb_2O_3$  doped silicon dioxide layer is then formed on the wafer using a chemical vapor

1 deposition (CVD) process. Antimony is then diffused from  
2 the doped silicon dioxide layer into the silicon within the  
3 window region.

4 Unfortunately, it is difficult to control the dopant  
5 concentration of the doped regions formed in the silicon  
6 with great precision using this technique. Further, when  
7 using this technique, small regions are formed in the doped  
8 silicon dioxide layer having large  $Sb_2O_3$  concentrations.  
9 These high dopant concentration regions are known to cause  
10 defects in the mask layer, thus causing antimony doped  
11 regions in the substrate underneath the mask layer where  
12 antimony is not desired.

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14  
15 The invention provides a method for forming a bipolar  
16 integrated circuit having a buried layer with a low defect  
17 density and a low resistivity. This is accomplished by  
18 covering a semiconductor wafer (typically silicon) with a  
19 thin silicon dioxide layer. The wafer is then subjected to  
20 ion implantation during which the thin silicon dioxide layer  
21 absorbs most of the implanted ions and hence most of the  
22 implant damage, leaving the semiconductor crystal lattice  
23 relatively damage free. A thick silicon dioxide layer is  
24 then deposited over the thin silicon dioxide layer in a low  
25 temperature deposition process. After that, the wafer is  
26 heated, which causes the semiconductor material to become  
27 annealed and which also causes the ions previously implanted  
28 into the thin silicon dioxide layer to diffuse into the  
29 semiconductor material to a desired junction depth. The  
30 thick silicon dioxide layer prevents dopants from diffusing  
31 into the atmosphere. Because the dopants diffuse through  
32 silicon dioxide relatively slowly, and preferentially  
33 diffuse into the semiconductor wafer, the loss of dopants  
34 into the thick silicon dioxide layer is minimal.

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36 Thereafter, the thin and thick silicon dioxide layers  
37 are removed and an epitaxial layer is deposited on the  
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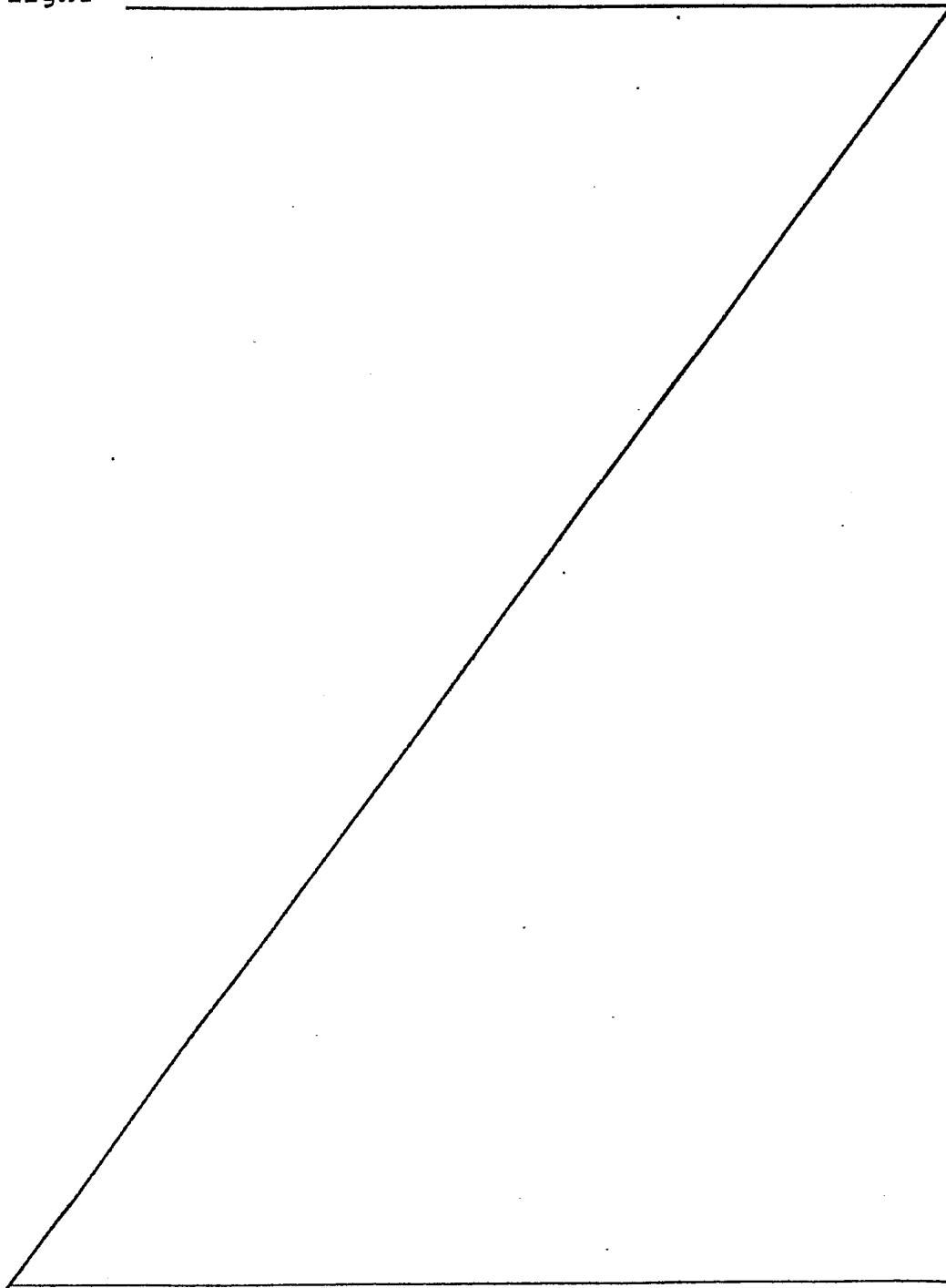
wafer. Isolation regions are then formed in the epitaxial layer to electrically isolate an area in the epitaxial layer where a bipolar transistor is to be formed. Base and emitter regions are then formed, e.g. by ion implantation. In this way, a transistor is provided having a buried layer with a low defect density and low resistivity.

The invention is further explained below, by way of example, with reference to the accompanying drawings, in which Figures 1 to 13 are cross sectional illustrations of successive stages of a process of manufacturing a bipolar transistor in accordance with the present invention.

The illustrated process for manufacturing a bipolar transistor in accordance with the present invention begins with the step of forming a silicon dioxide layer 12 on a semiconductor wafer 10 (Figure 1). In one embodiment of the invention, semiconductor wafer 10 has a silicon substrate 11 having a [100] crystal orientation, a P type conductivity, and a resistivity of 25 to 45 ohm-centimeters. However, other semiconductor materials having either P or N type conductivity and having other resistivities can also be used. In one embodiment of the invention, silicon dioxide layer 12 is about 1,000 Å thick and is formed by heating wafer 10 to a temperature of about 1100°C in an oxygen atmosphere for approximately 3.5 hours. A silicon nitride layer 14 is then formed on wafer 10. In one embodiment, silicon nitride layer 14 is about 1500 Å thick and is formed by a chemical vapor deposition (CVD) process. As described below, silicon nitride layer 14 serves as a mask during the formation of buried layer 22 (Figure 5). Silicon dioxide layer 12 serves as an intermediate layer which prevents mechanical stress caused by the difference in thermal expansion of silicon substrate 11 and silicon nitride

layer 14.

Referring to Figure 2, wafer 10 is covered with a photoresist layer 15, which is selectively exposed to light



1 and developed, thereby forming a window region 16 and  
2 exposing a portion of silicon nitride layer 14. Window 16  
3 defines the area where buried layer 22 will subsequently be  
4 formed.

5 The portion of silicon nitride layer 14 and silicon  
6 dioxide layer 12 under window 16 is then removed using  
7 conventional etching techniques, and remaining photoresist  
8 15 is removed, leaving the structure of Figure 3. In one  
9 embodiment, the exposed portion of silicon nitride 14 is  
10 removed in a plasma etching process and the portion of  
11 silicon dioxide 12 lying thereunder is removed with hydro-  
12 flouric acid.

13  
14 Referring to Figure 4, a silicon dioxide layer 18 is  
15 formed in window 16. In one embodiment, silicon dioxide  
16 layer 18 is about 250A thick and is formed by heating wafer  
17 10 to about 950°C in an oxygen atmosphere for approximately  
18 40 minutes. In accordance with one novel feature of this  
19 invention, wafer 10 is then subjected to an ion implantation  
20 process. Typically antimony ions are implanted into silicon  
21 dioxide layer 18 with an energy of about 50 KEV and a dosage  
22 of about  $3 \times 10^{15}$  ions/cm<sup>2</sup>. However, other ions, implant  
23 energy, and dosages could also be used. During this  
24 process, it has been estimated that 85% of the antimony ions  
25 reaching window region 16 are implanted into silicon dioxide  
26 layer 12 with the remaining 15% implanted into silicon  
27 substrate 11. Because of this, damage to the crystal  
28 lattice of substrate 11 is less than the damage which would  
29 occur if the ions were all implanted into substrate 11.

30  
31 Ions implanted into silicon dioxide layer 18 are  
32 subsequently diffused into silicon substrate 11 to form a  
33 buried layer as described below. Of importance, ions  
34 striking wafer 10 outside of window region 16 lodge in  
35 either silicon nitride layer 14 or silicon dioxide layer  
36 12. Because of the thickness of layers 12 and 14, during  
37 this subsequent diffusion step, ions do not diffuse from  
38

1 layers 12 and 14 into substrate 11. In this way, layers 12  
2 and 14 confine the formation of the buried layer to the area  
3 defined by window 16.

4  
5 Referring to Figure 5, a layer of material such as  
6 silicon dioxide layer 20 is then formed on wafer 10. In one  
7 embodiment, silicon dioxide layer 20 is about 3,000Å thick  
8 and is deposited via a CVD process. Of importance, this is  
9 done at a low temperature, e.g., 425°C, so that implanted  
10 dopants do not diffuse out of silicon dioxide layer 18 into  
11 the atmosphere. Thereafter, wafer 10 is subjected to a  
12 combination annealing/drive-in diffusion process.  
13 Specifically, wafer 10 is baked at about 1250°C for about 17  
14 minutes in an inert gas, e.g. nitrogen or argon. During  
15 this process, antimony ions diffuse out of silicon dioxide  
16 layer 18 and into silicon substrate 11 thus forming N type  
17 region 22 (the buried layer). Buried layer 22 is thus  
18 formed to a thickness of about 3μ, but if a thicker buried  
19 layer is desired, a longer baking time is used. It is noted  
20 that by limiting the baking time, lateral diffusion of  
21 buried layer 22 is minimized. Silicon dioxide layer 20  
22 prevents out diffusion of antimony into the atmosphere  
23 during this process. Because the implanted dopants diffuse  
24 through silicon dioxide slowly, the loss of dopants diffused  
25 into silicon dioxide layer 20 is minimal. Table I below  
26 indicates the junction depth between the antimony doped  
27 region 22 of substrate 11 and the P doped portion of  
28 substrate 11 for baking times of 18 minutes and 74 minutes  
29 for various conditions. (The data of Table I is from a  
30 computer simulation.) As can be seen in Table I, the sheet  
31 resistance of the buried layer is lower when using silicon  
32 dioxide layer 20 than when not using layer 20.

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TABLE I\*

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				Junction	Buried Layer Sheet Resistance
	Layer 18	Layer 20	Anneal Time**	Depth	
6	not present	not present	18 min.	3 $\mu$	24 $\Omega$ /square
7	not present	3,000A	18 min.	3 $\mu$	20 $\Omega$ /square
8	250A	not present	18 min.	3 $\mu$	23 $\Omega$ /square
9	250A	3,000A	18 min.	3 $\mu$	19 $\Omega$ /square
10	300A	3,000A	74 min.	5 $\mu$	20 $\Omega$ /square
11	300A	not present	74 min.	5 $\mu$	27 $\Omega$ /square

\*Drive in temperature is 1,250°C

\*\*Includes a ramp-up time of 50 minutes while temperature increases from 750°C to 1,250°C at a rate of 10°C/minutes and a ramp-down time of 120 minutes while the temperature falls from 1,250°C to 830°C.

Thereafter, silicon dioxide layers 12, 18 and 20 and silicon nitride layer 14 are removed, leaving N type region 22 doped with antimony in P type substrate 11.

An epitaxial layer is then formed on wafer 10, and a bipolar transistor is formed in the epitaxial layer. In one process for forming the bipolar transistor, an N type epitaxial layer 24 (Figure 6) is then formed on wafer 10. In one embodiment, epitaxial layer is approximately 2 microns thick and is deposited by a CVD process. Epitaxial layer 24 typically has a conductivity of about 0.5 ohm-centimeters. A silicon dioxide layer 26 and a silicon nitride layer 28 are then formed on wafer 10. In one embodiment of the invention, silicon dioxide layer 26 is thermally grown to a thickness of about 1,000A by heating wafer 10 to a temperature of about 950°C in an oxygen atmosphere for approximately 1/3 hours. Silicon nitride layer 28 is typically 1500A thick and is deposited by a CVD process.

Wafer 10 then is coated with a photoresist layer 30 (Figure 7), and selectively exposed to light. The exposed



1 portions of photoresist layer 30 are then removed, leaving  
2 windows 32 and 33. (Although drawn as two windows, window  
3 32 is really a single window surrounding buried layer 22.)  
4 Window 32 defines the area where an isolation region is to  
5 be formed in wafer 10. Window 33 defines where a second  
6 silicon dioxide region is to be formed which prevents a  
7 highly doped collector contact region from forming a capaci-  
8 tive PN junction with the to-be-formed transistor base  
9 region. The portion of silicon dioxide layer 26 and silicon  
10 nitride layer 28 underneath windows 32 and 33 is removed via  
11 a conventional plasma etching process using, for example,  
12  $\text{CF}_4$  as the process gas. In addition, an 8000 to 9000Å thick  
13 portion of epitaxial layer 24 under windows 32 and 33 is  
14 also removed via a plasma etching process using, for  
15 example,  $\text{SF}_6$  as the process gas. The remaining portion of  
16 photoresist layer 30 is then removed, and isolation regions  
17 34 and 35 are formed in windows 32 and 33, respectively  
18 (Figure 8). In one embodiment, isolation regions 34 and 35  
19 are silicon dioxide between 1.8 and 2 microns thick and are  
20 grown by heating wafer 10 to a temperature of 920°C for 2½  
21 to 3 hours in steam at high pressure (about 15 atmos-  
22 pheres). Of importance, approximately 55% of isolation  
23 regions 34 and 35 grow into epitaxial layer 24 while the  
24 remainder grows into window 32. Thus, the top of isolation  
25 region 34 is roughly coplanar with the top of epitaxial  
26 layer 24.

27

28 Referring to Figure 9, silicon nitride region 28 is  
29 removed (typically with phosphoric acid) and silicon dioxide  
30 layer 26 is removed (typically with hydrofluoric acid).  
31 During removal of silicon dioxide layer 26, small amounts of  
32 silicon dioxide from regions 34 and 35 are also removed.  
33 However, these amounts represent a negligible portion of  
34 regions 34 and 35.

35

36 Referring to Figure 9, a silicon dioxide layer 36  
37 (typically about 2900Å thick) is grown on wafer 10. In one  
38

1 embodiment, this is done by heating the wafer to a  
2 temperature of about 1050°C in steam for about 20 to 25  
3 minutes.

4  
5 Referring to Figure 10, wafer 10 is then coated with a  
6 photoresist layer 37. Photoresist layer 37 is then  
7 patterned leaving a window 38 which defines the base region  
8 of the to-be-formed bipolar transistor. In one embodiment,  
9 the exposed portion of wafer 10 is then subjected to an ion  
10 implantation process which results in the formation of a P  
11 type base region 40. In one embodiment, boron ions are  
12 used, with an implant energy of about 150 KEV and a dosage  
13 between about  $4 \times 10^{13}$  and  $8 \times 10^{13}$  ions/cm<sup>2</sup>. Photoresist  
14 layer 37 is then removed. Referring to Figure 11, wafer 10  
15 is then coated with another photoresist layer 42 which is  
16 selectively patterned leaving windows 44a and 44b. Window  
17 44a defines an emitter region 46 which in one embodiment is  
18 formed during an ion implantation process using, for  
19 example, arsenic ions, an implant energy of approximately 50  
20 KEV, and a dosage between  $1 \times 10^{16}$  and  $3 \times 10^{16}$  ions/cm<sup>2</sup>.  
21 The portion of epitaxial layer 24 within window 44b is also  
22 implanted with ions during this process, thus facilitating  
23 formation of a collector contact for the transistor. Photo-  
24 resist layer 42 is then removed.

25  
26 Openings 48 (Figure 12) are then etched in silicon  
27 dioxide layer 36, e.g. by coating wafer 10 with a  
28 photoresist layer 49, and selectively exposing photoresist  
29 layer 49 and removing the exposed portions, thereby exposing  
30 portions of silicon dioxide layer 36. The exposed portions  
31 of silicon dioxide layer 36 are then removed using, for  
32 example, a buffered HF solution, leaving openings 48.  
33 Photoresist layer 49 is then removed.

34  
35 Referring to Figure 13, a conductive layer 50 (such as  
36 metal or polycrystalline silicon) is then formed on wafer 10  
37 and patterned, e.g. by covering the wafer with photoresist  
38

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1 (not shown), patterning the photoresist, thereby exposing  
2 portions of conductive layer 50, and removing the exposed  
3 portions. The photoresist is then removed, leaving a  
4 bipolar transistor 54 in which conductive layer 50 makes  
5 electrical contact with base 40, emitter 46, and collector  
6 47. Low resistance buried layer 22 isolates transistor 54  
7 from substrate 11. In addition, collector 47 is connected  
8 to the collector contact via buried layer 22.  
9

10 While the invention has been described with reference  
11 to a specific embodiment, those skilled in the art will  
12 recognize that modifications can be made to form and detail  
13 without departing from the scope of the  
14 invention. For example, layers 12 and 14 can be formed from  
15 substances other than silicon dioxide and silicon nitride,  
16 and can have thicknesses other than those described. In  
17 addition, ions other than antimony can be used and a wafer  
18 having a crystal orientation other than a [100] orientation  
19 can be used. In addition, the starting material can be  
20 either P type or N type. Accordingly, all such changes come  
21 within the present invention.  
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## CLAIMS

1. A process of manufacturing a bipolar transistor having a buried layer (22) comprising the steps of forming a doped region in semiconductor material (11), forming an epitaxial layer (24) over the doped region, and forming a bipolar transistor in the epitaxial layer, the doped region serving as a buried layer (22), characterized by the steps of:
- forming a layer (18) of a first material over the semiconductor material prior to the step of forming the epitaxial layer;
- implanting ions into the layer (18) of first material; and
- diffusing the ions out of the layer (18) of the first material and into the semiconductor material (11), thereby forming the doped region (22).
2. A process as claimed in claim 1 wherein the semiconductor material is silicon.
3. A process as claimed in claim 1 or 2 comprising the further step of forming a layer (20) of a second material over the layer of the first material, the layer (20) of the second material preventing out diffusion of ions into the atmosphere during the step of diffusing the ions.
4. A process as claimed in claim 3 wherein the first and second materials are silicon dioxide.
5. A process as claimed in claim 4 wherein the layer (20) of the second material is formed by a chemical vapor deposition process.
6. A process as claimed in claim 5 wherein the layer (20) of the second material is deposited at a temperature less than 700°C.
7. A process as claimed in any preceding claim comprising the further steps of:
- forming a layer (12,14) of a third material on

the wafer before forming the layer of the first material; and

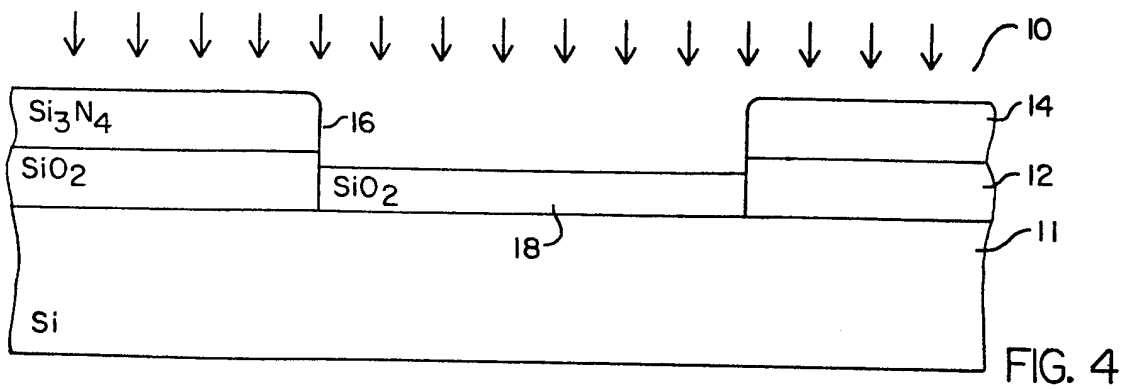
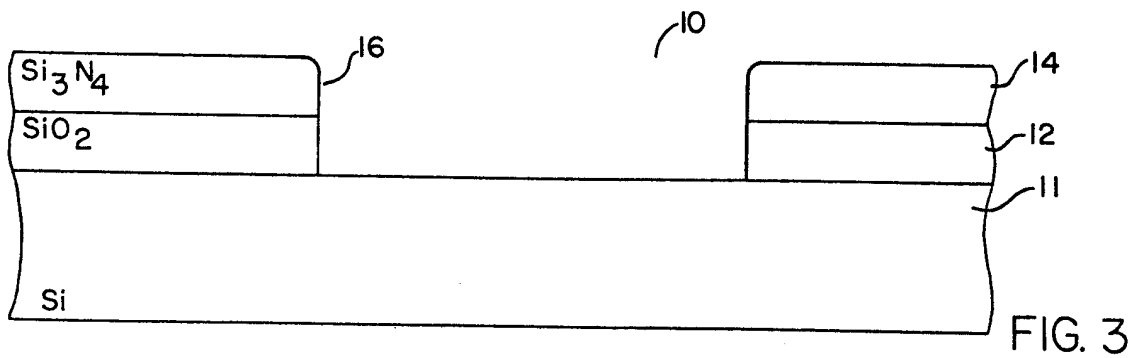
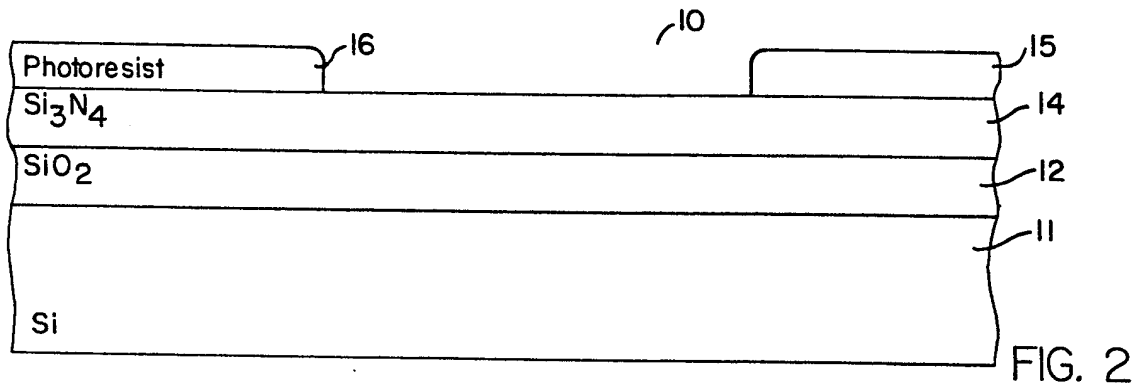
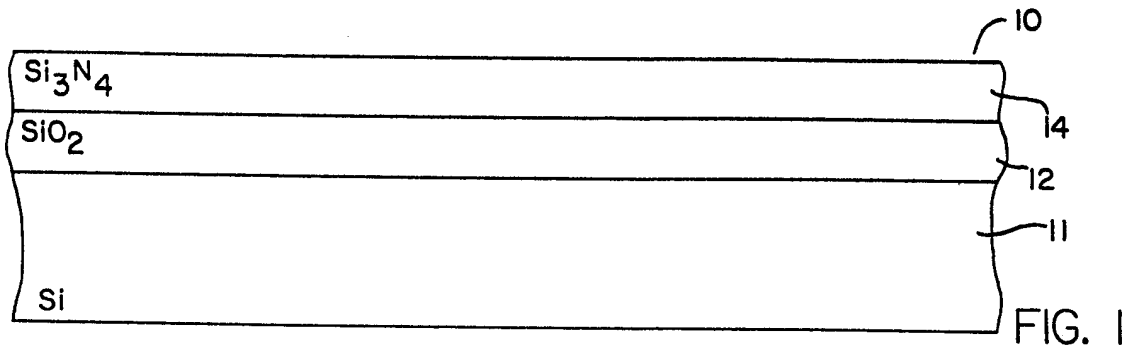
5 etching a window region (16) in the layer (12,14) of the third material, the layer (18) of the first material being formed in the window region, the layer (12,14) of the third material being thicker than the layer (18) of the first material, ions being implanted into the layer (12,14) of the third material during the step of  
10 implanting ions, but not diffusing from the layer (12,14) of third material into the semiconductor material (11) during the step of diffusing the ions.

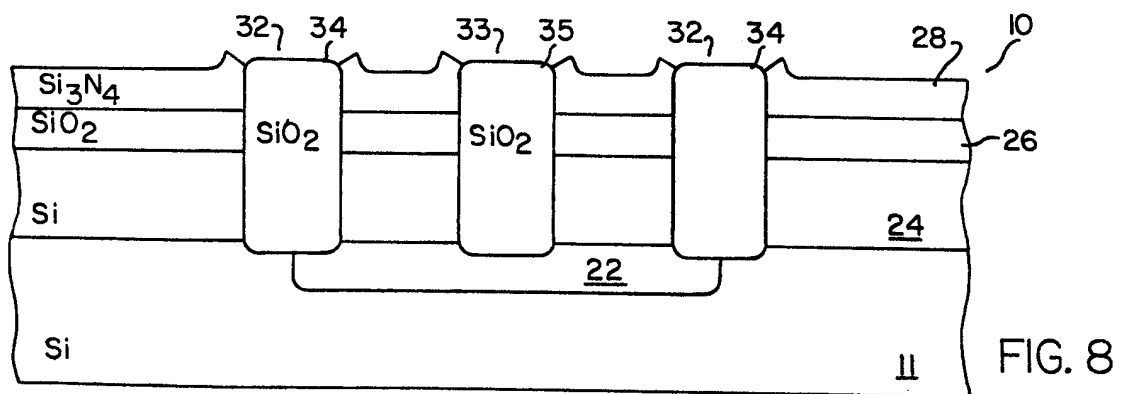
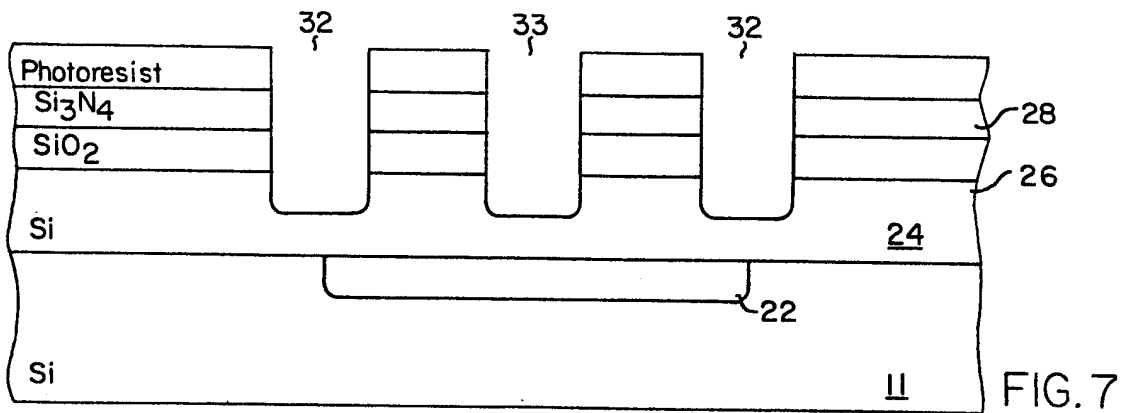
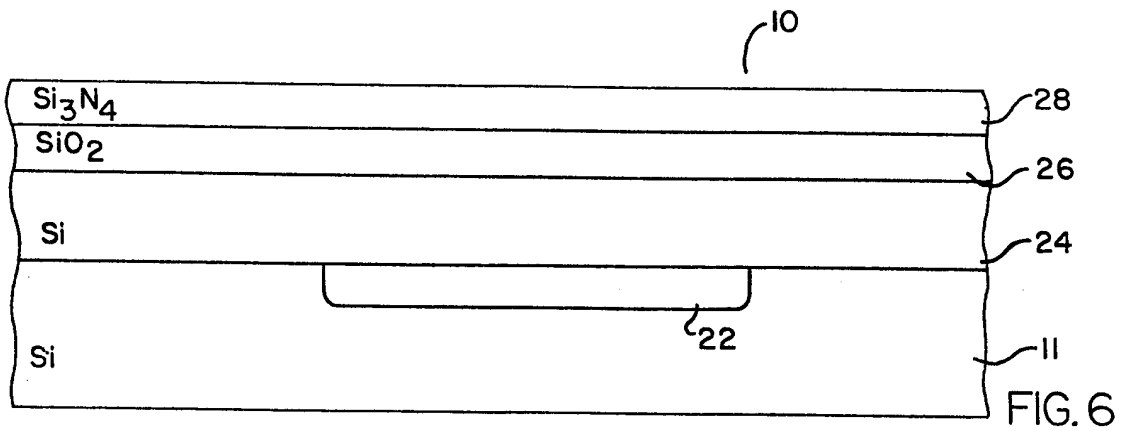
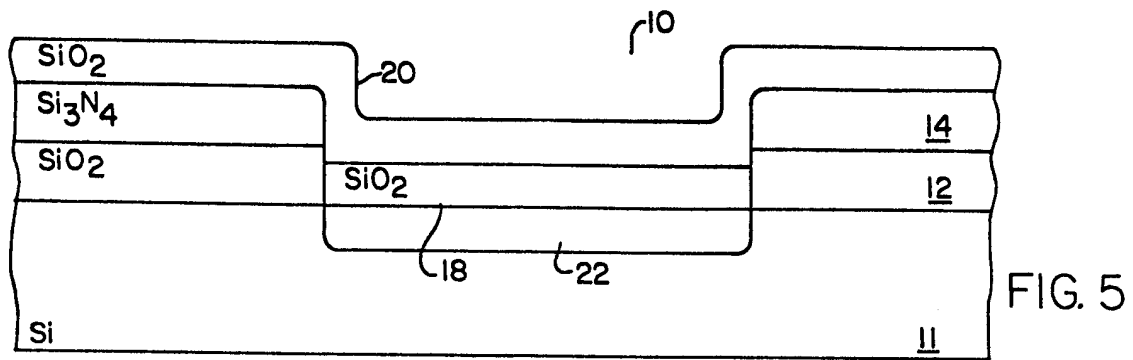
8. A process as claimed in claim 7 wherein the  
15 third material comprises silicon dioxide.

9. A process as claimed in claim 7 or 8 wherein the third material comprises silicon nitride.

10. A process as claimed in claim 7, 8 or 9 wherein the layer (12,14) of the third material is  
20 removed prior to the formation of the epitaxial layer (24).







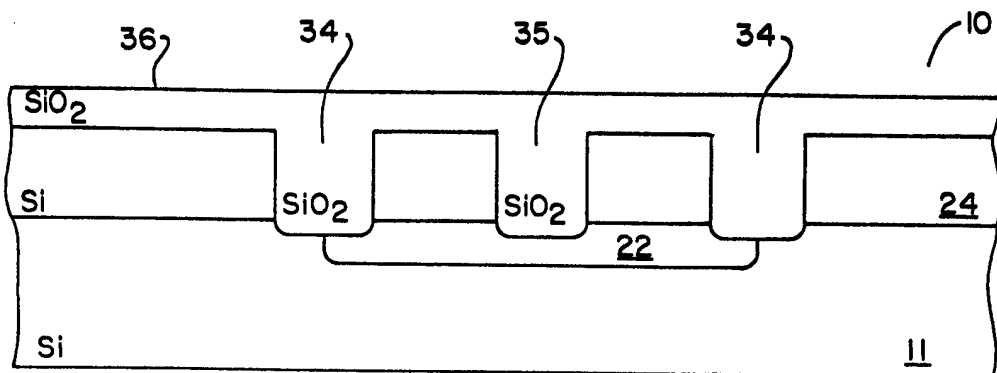


FIG. 9

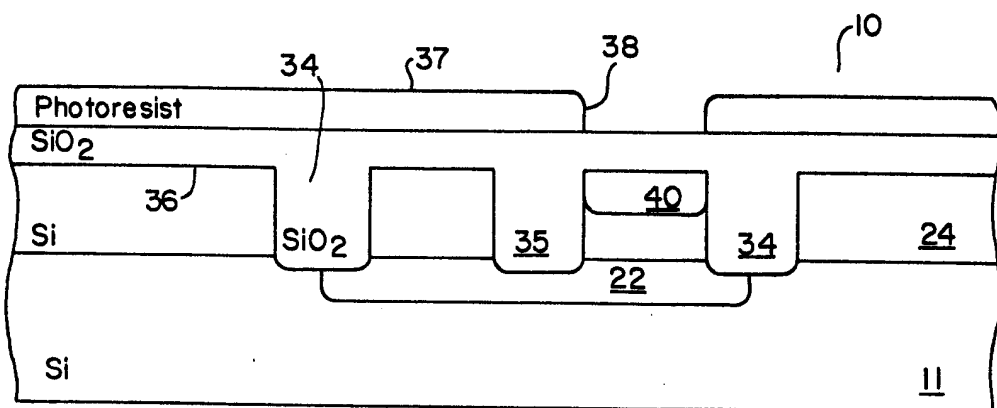


FIG. 10

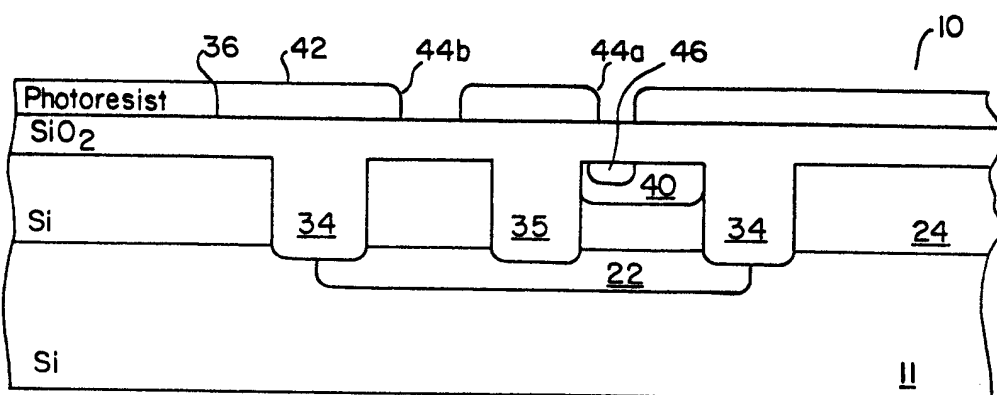


FIG. 11

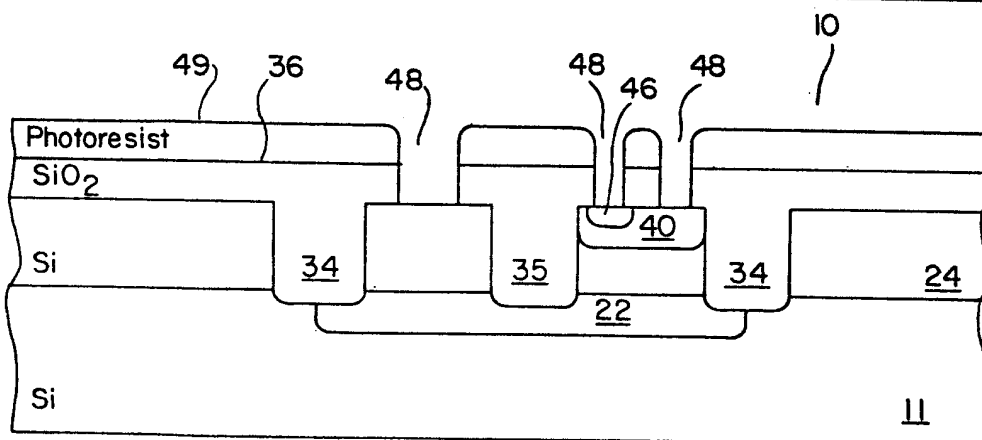


FIG. 12



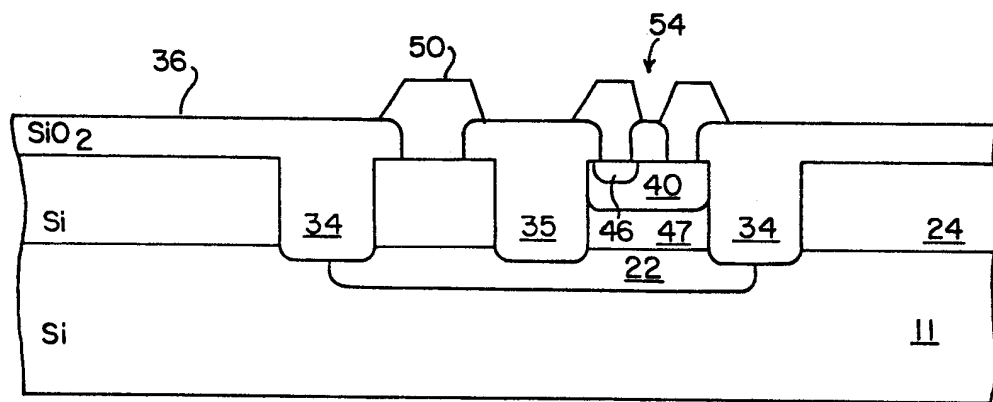


FIG. 13